

providing said first and second regions with a
crystallization promoting material comprising a metal for
promoting crystallization of said semiconductor film;

heating said semiconductor film with said crystallization
promoting material to crystallize said semiconductor film,

wherein crystals grow from said first region to said second
region and the growth of the crystals terminates at said second
region.

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3. (New) The method according to claim 2 wherein said
metal is selected from the group consisting of Fe, Co, Ni, Ru,
Rh, Pd, Os, Ir, Pt, Cu and Au.

4. (New) A method of manufacturing an electroluminescence
device comprising the steps of:

forming a semiconductor film comprising amorphous silicon
on an insulating surface, said semiconductor film having a first
region and a second region;

providing said first and second regions with a
crystallization promoting material comprising a metal for
promoting crystallization of said semiconductor film;

heating said semiconductor film with said crystallization
promoting material to crystallize said semiconductor film,

wherein crystals grow from said first region to said second region and the growth of the crystals terminates at said second region.

5. (New) The method according to claim 4 wherein said metal is selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu and Au.

6. (New) A method of manufacturing a semiconductor device comprising the steps of:

*As
contd* forming a semiconductor film comprising amorphous silicon on an insulating surface, said semiconductor film having a first region and a second region;

providing said first and second regions with a crystallization promoting material comprising a metal for promoting crystallization of said semiconductor film;

heating said semiconductor film with said crystallization promoting material to crystallize said semiconductor film, wherein crystals grow from said first region substantially in parallel to said insulating surface,

wherein said second region functions as a stopper for terminating the crystallization from said first region.

7. (New) The method according to claim 6 wherein said metal is selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu and Au.

8. (New) A method of manufacturing an electroluminescence display device comprising the steps of:

forming a semiconductor film comprising amorphous silicon on an insulating surface, said semiconductor film having a first region and a second region;

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providing said first and second regions with a crystallization promoting material comprising a metal for promoting crystallization of said semiconductor film;

heating said semiconductor film with said crystallization promoting material to crystallize said semiconductor film, wherein crystals grow from said first region substantially in parallel to said insulating surface,

wherein said second region functions as a stopper for terminating the crystallization from said first region.

9. (New) The method according to claim 6 wherein said metal is selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu and Au.

10. (New) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising amorphous silicon on an insulating surface, said semiconductor film having a first stripe-shaped region and a second stripe-shaped region arranged in parallel with each other;

providing said first and second stripe-shaped regions with a crystallization promoting material comprising a metal for promoting crystallization of said semiconductor film;

heating said semiconductor film with said crystallization promoting material to crystallize said semiconductor film,

wherein widths of said first and second stripe-shaped regions are different from each other.

11. (New) The method according to claim 10 wherein said metal is selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu and Au.

12. (New) A method of manufacturing an electroluminescence display device comprising the steps of:

forming a semiconductor film comprising amorphous silicon on an insulating surface, said semiconductor film having a first stripe-shaped region and a second stripe-shaped region arranged in parallel with each other;

providing said first and second stripe-shaped regions with a crystallization promoting material comprising a metal for promoting crystallization of said semiconductor film;

heating said semiconductor film with said crystallization promoting material to crystallize said semiconductor film,

wherein widths of said first and second stripe-shaped regions are different from each other.

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13. (New) The method according to claim 12 wherein said metal is selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu and Au.

14. (New) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising amorphous silicon on an insulating surface, said semiconductor film having at least first, second and third stripe-shaped regions arranged in parallel with one another wherein said second stripe-shaped region is located between said first and third stripe-shaped regions;

providing said first, second and third stripe-shaped regions with a crystallization promoting material comprising a metal for promoting crystallization of said semiconductor film;

heating said semiconductor film with said crystallization promoting material to crystallize said semiconductor film,

wherein a width of said second stripe-shaped region is smaller than widths of said first and third stripe-shaped regions.

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15. (New) The method according to claim 14 wherein said metal is selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu and Au.

16. (New) A method of manufacturing an electroluminescence display device comprising the steps of:

forming a semiconductor film comprising amorphous silicon on an insulating surface, said semiconductor film having at least first, second and third stripe-shaped regions arranged in parallel with one another wherein said second stripe-shaped region is located between said first and third stripe-shaped regions;

providing said first, second and third stripe-shaped regions with a crystallization promoting material comprising a metal for promoting crystallization of said semiconductor film;

heating said semiconductor film with said crystallization promoting material to crystallize said semiconductor film,

wherein a width of said second stripe-shaped region is smaller than widths of said first and third stripe-shaped regions.

17. (New) The method according to claim 16 wherein said metal is selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu and Au.--

REMARKS

Entry of these additional new claims prior to initial examination is requested.

Applicant also calls attention to the enclosed document listed on the attached form PTO-1449. Official consideration and citation is requested.